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(54) **Title**: METHODS OF FORMING BURIED MICROELECTRICOMECHANICAL STRUCTURES COUPLED WITH DEVICE SUBSTRATES AND STRUCTURES FORMED THEREBY

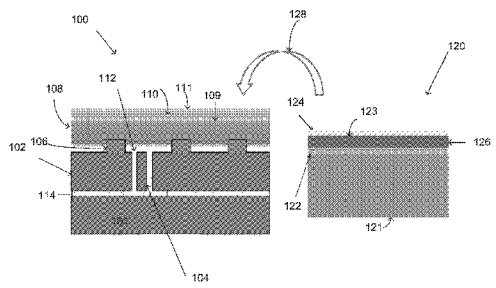


FIG. 1a

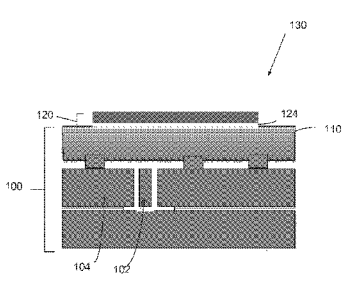


FIG. 1b

(57) **Abstract**: Methods of forming integrated MEMS structures are described. Those methods and structures may include forming at least one MEMS structure on a first substrate, forming a first bonding layer on a top surface of die first substrate, and then coupling the first bonding layer disposed on the first substrate to a second substrate, wherein the second substrate comprises a device layer. The bonding may comprise a layer transfer process, wherein an integrated MEMS device is formed.

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